



Attorney Docket No.: 5308-413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler et al.

Application No.: 10/849,617

Filed: May 20, 2004

For: METHODS OF FABRICATING NITRIDE-BASED TRANSISTORS HAVING  
REGROWN OHMIC CONTACT REGIONS AND NITRIDE-BASED  
TRANSISTORS HAVING REGROWN OHMIC CONTACT REGIONS

Confirmation No.: 9882

Group Art Unit: 2811

Examiner: Unknown

Date: January 25, 2005

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**PRELIMINARY AMENDMENT**

Sir:

Applicant provides the present Preliminary Amendment to correct typographic errors in the present application.

Amendments to the specification begin on page 2 of this paper.